

UNA0216 (UN216)

Transistor array to drive the small motor

Features

- Small and lightweight
- Low power consumption (low $V_{CE(sat)}$ transistor used)
- Low-voltage drive
- With 6 elements incorporated. (SO-14)

Applications

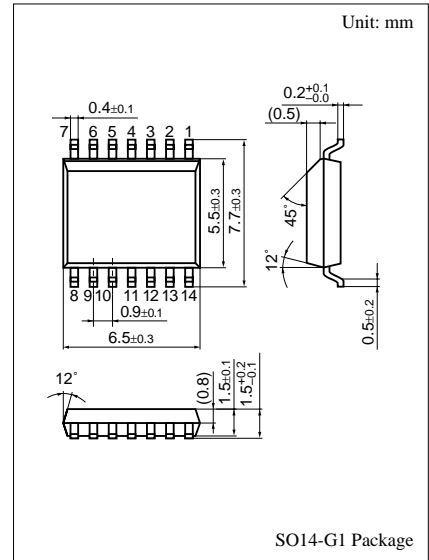
- Video cameras
- Cameras
- Portable CD players
- Small motor drive circuits in general for electronic equipment.

Absolute Maximum Ratings ($T_a=25\pm 2^\circ\text{C}$)

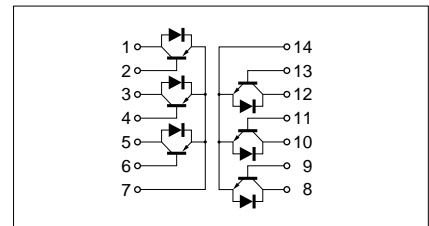
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	± 12	V
Collector to emitter voltage	V_{CEO}	± 10	V
Emitter to base voltage	V_{EBO}	± 7	V
Collector current	I_C	± 3	A
Total power dissipation	P_T^*	0.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note: \pm marks used above: +: NPN part, -: PNP part

* $T_C = 25^\circ\text{C}$ only when the elements are active



Internal Connection



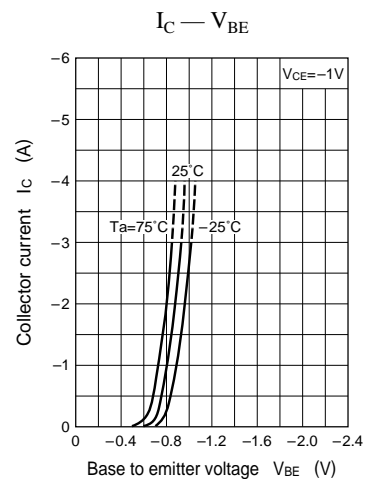
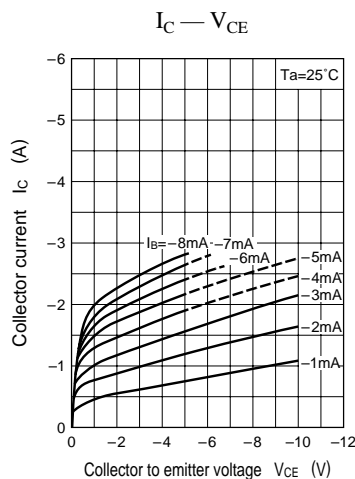
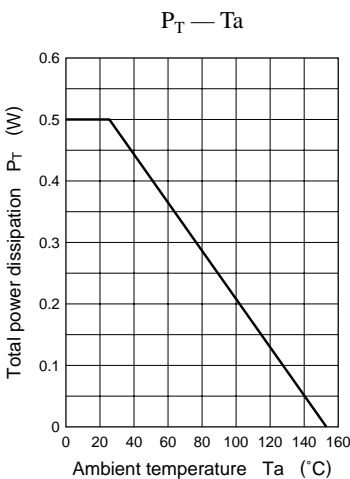
Note.) The Part number in the Parenthesis shows conventional part number.

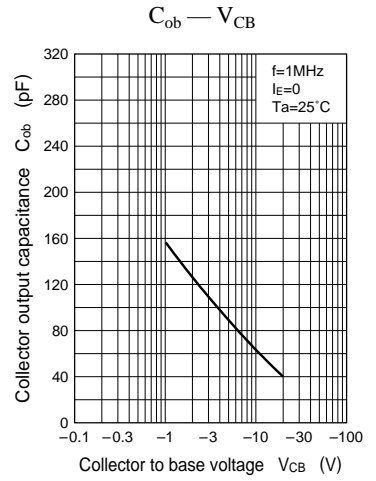
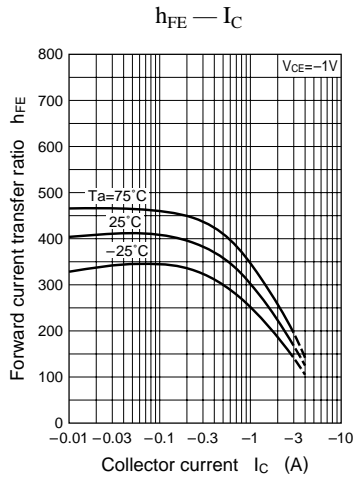
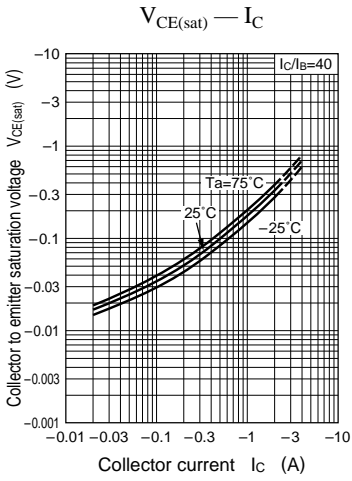
■ Electrical Characteristics (Ta=25±2°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I _{CBO}	(NPN) V _{CB} = 10V			1	μA
		(PNP) V _{CB} = -10V			-1	
Collector to base voltage	V _{CBO}	(NPN) I _C = 10μA	12			V
		(PNP) I _C = -10μA	-12			
Collector to emitter voltage	V _{CEO}	(NPN) I _C = 1mA	10			V
		(PNP) I _C = -1mA	-10			
Emitter to base voltage	V _{EBO}	(NPN) I _E = 10μA	7			V
		(PNP) I _E = -10μA	-7			
Forward current transfer ratio	h _{FE}	(NPN) V _{CE} = 1V, I _C = 0.5A*	200		800	
		(PNP) V _{CE} = -1V, I _C = -0.5A*	200		800	
Collector to emitter saturation voltage	V _{CE(sat)1}	(NPN) I _C = 2A, I _B = 50mA			0.25	V
		(PNP) I _C = -2A, I _B = -50mA			-0.45	
Transition frequency	f _T	(NPN) V _{CB} = 6V, I _E = -50mA, f = 200MHz		150		MHz
		(PNP) V _{CB} = -6V, I _E = 50mA, f = 200MHz		150		
Collector output capacitance	C _{ob}	(NPN) V _{CB} = 10V, I _E = 0, f = 1MHz		50		pF
		(PNP) V _{CB} = 10V, I _E = 0, f = 1MHz		65		
Forward voltage (DC)	V _F	(NPN) I _F = 1A			1.5	V
		(PNP) I _F = -1A			1.5	

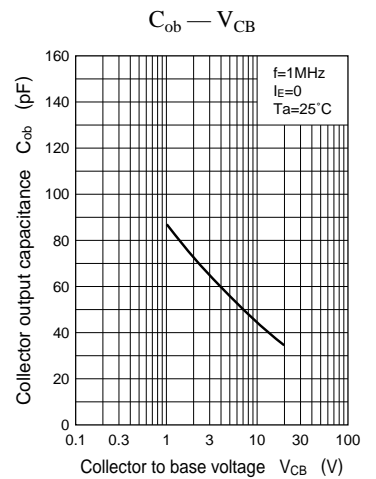
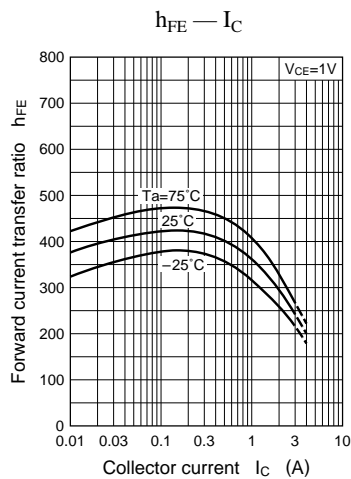
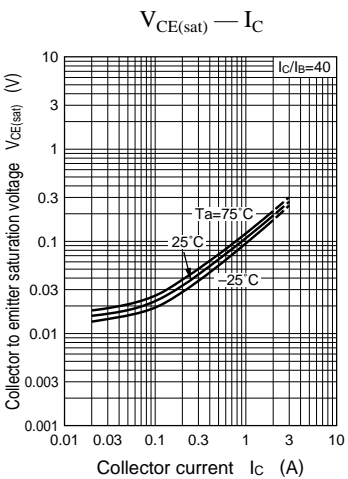
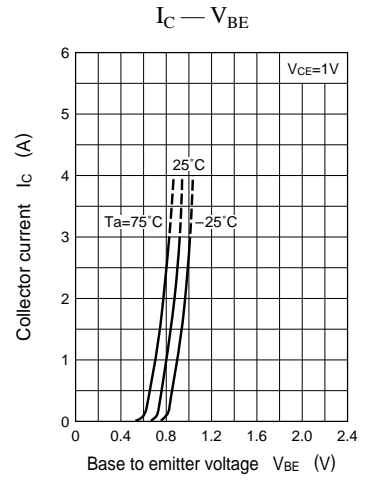
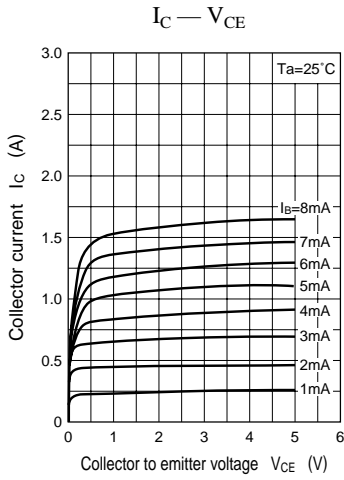
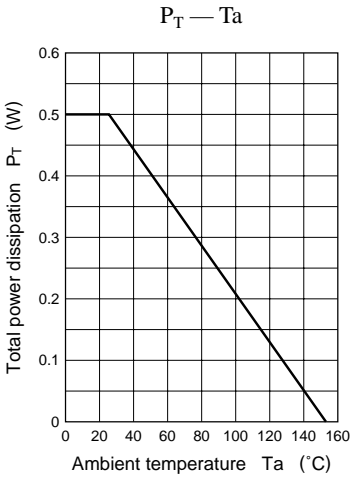
*Pulse measurement

Characteristics charts of PNP transistor block





Characteristics charts of NPN transistor block



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